Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

CHARACTERISTICS

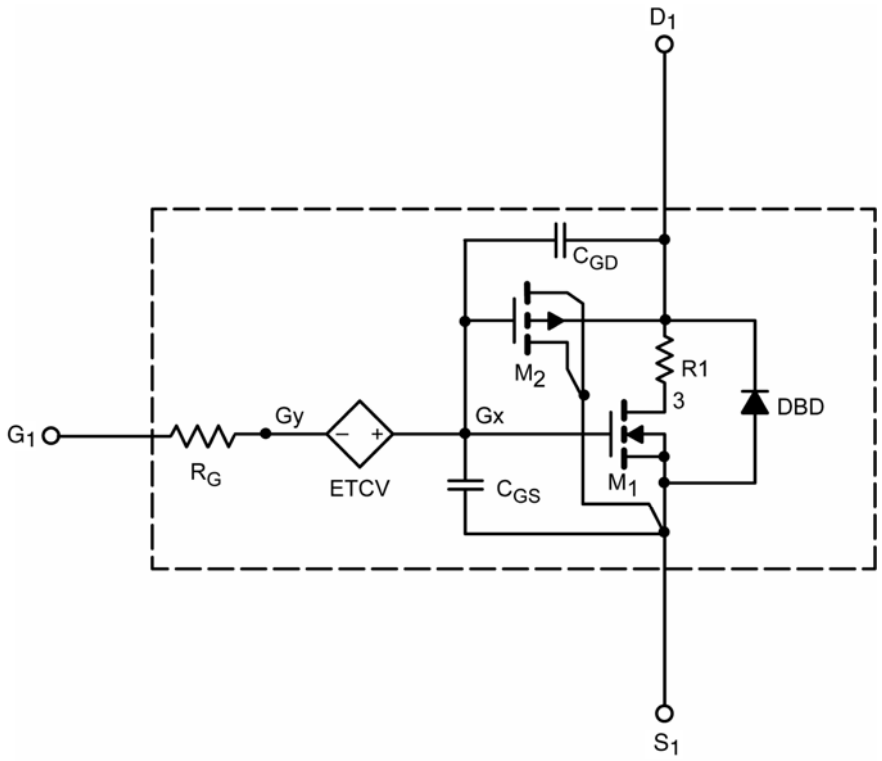
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the N-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

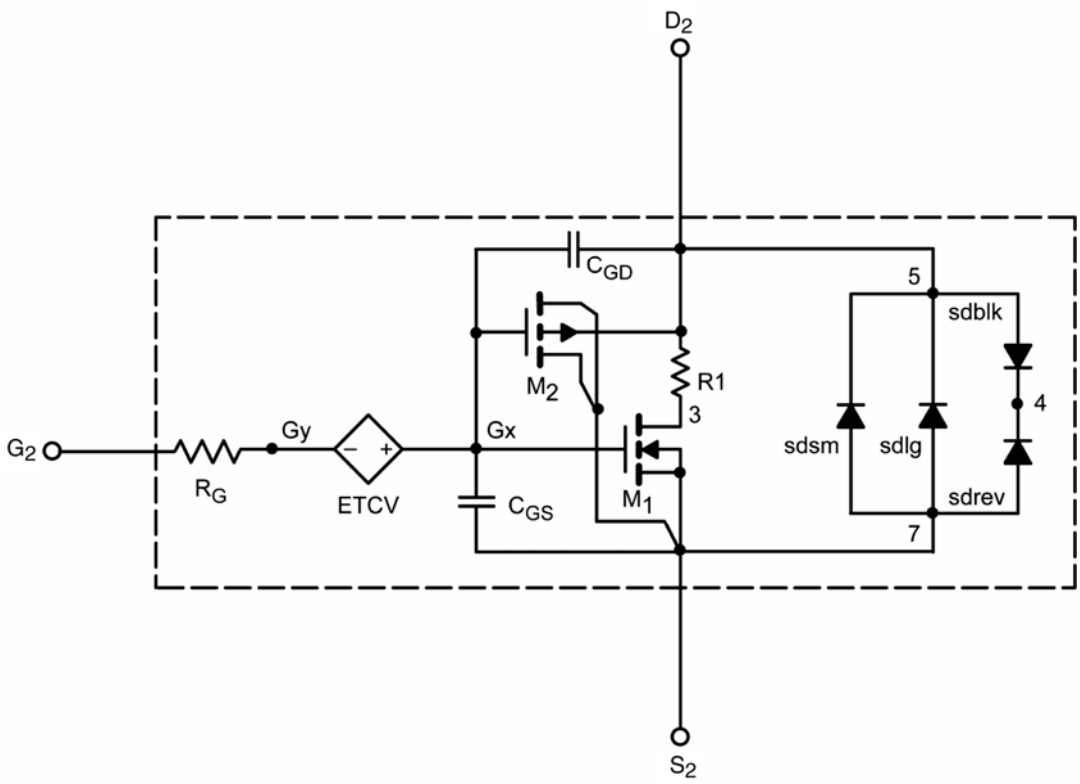
A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

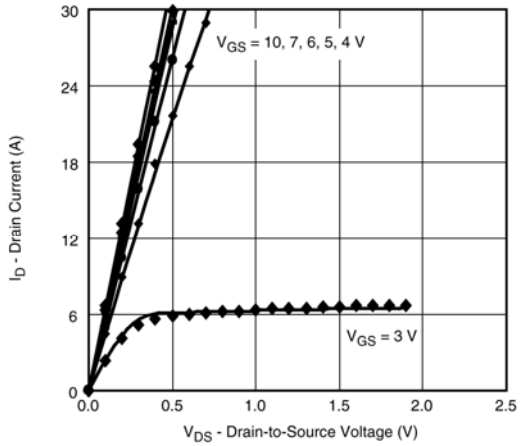
SUBCIRCUIT MODEL SCHEMATIC

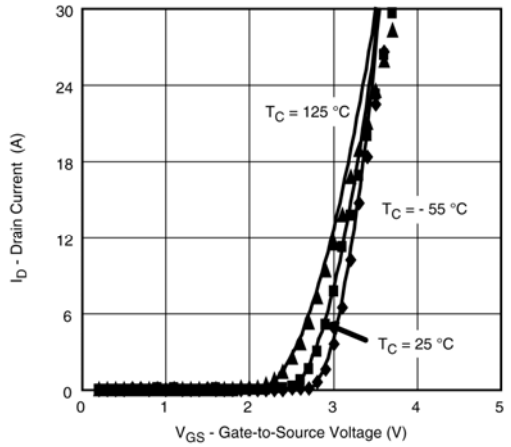


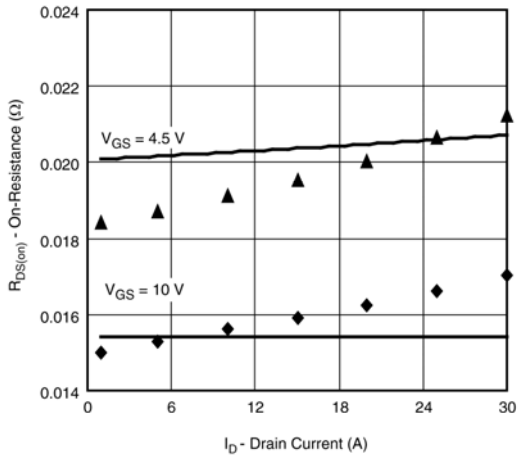
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Condition**		**Simulated Data**	**Measured Data**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	Ch-1	1.8		V
			Ch-2	1.8		
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 8 A	Ch-1	0.0154	0.0156	Ω
		V_{GS} = 10 V, I_D = 8 A	Ch-2	0.0154	0.0156	
		V_{GS} = 4.5 V, I_D = 5 A	Ch-1	0.020	0.019	
		V_{GS} = 4.5 V, I_D = 5 A	Ch-2	0.020	0.019	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 8 A	Ch-1	29	29	S
		V_{DS} = 15 V, I_D = 8 A	Ch-2	29	29	
Diode Forward Voltage[a]	V_{SD}	I_S = 1 A	Ch-1	0.74	0.74	V
		I_S = 1 A	Ch-2	0.46	0.46	
Dynamic[b]						
Input Capacitance	C_{iss}	Channel 1 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz Channel 2 V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	Ch-1	945	950	pF
			Ch-2	945	950	
Input Capacitance	C_{oss}		Ch-1	184	155	
			Ch-2	184	185	
Reverse Transfer Capacitance	C_{rss}		Ch-1	64	65	
			Ch-2	64	65	
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 8 A	Ch-1	14	16.5	nC
		V_{DS} = 15 V, V_{GS} = 10 V, I_D = 8 A	Ch-2	14	16.5	
		Channel-1 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 8 A Channel-2 V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 8 A	Ch-1	7	7.3	
			Ch-2	7	7.3	
Gate-Source Charge	Q_{gs}		Ch-1	2.7	2.7	
			Ch-2	2.7	2.7	
Gate-Drain Charge	Q_{gd}		Ch-1	2.1	2.1	
			Ch-2	2.1	2.1	

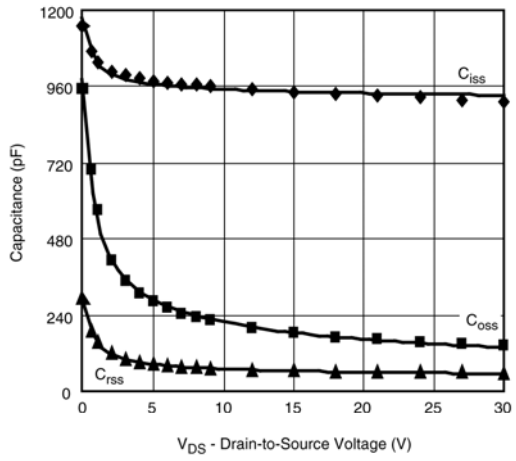
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

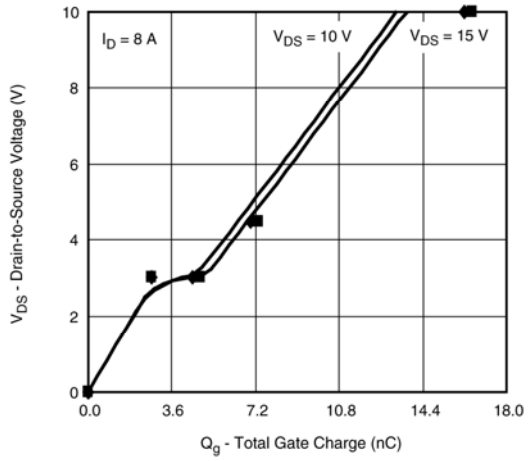
CHANNEL 1 - COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

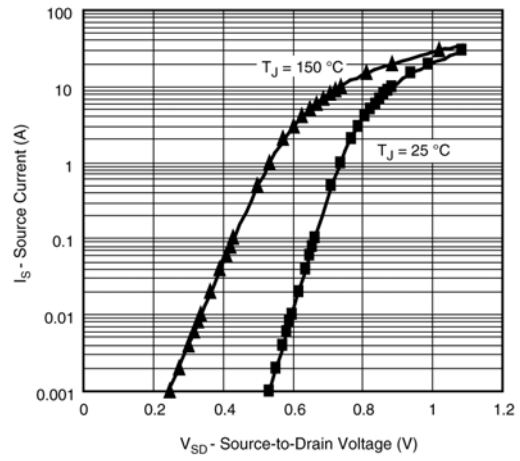












Note: Dots and squares represent measured data.

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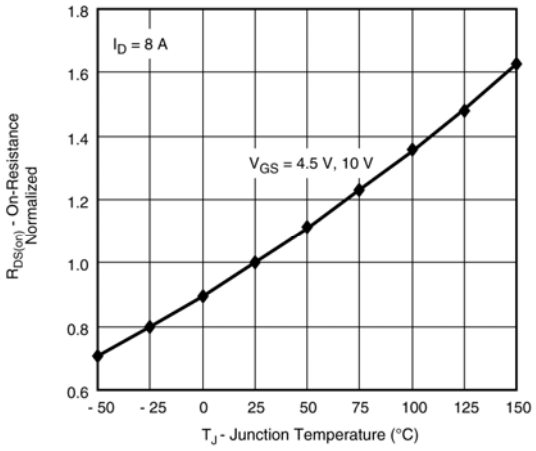
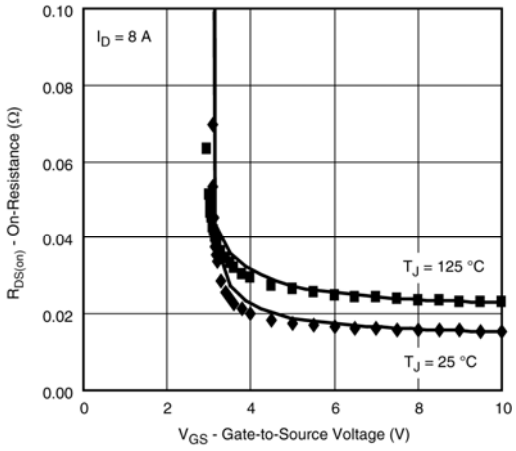
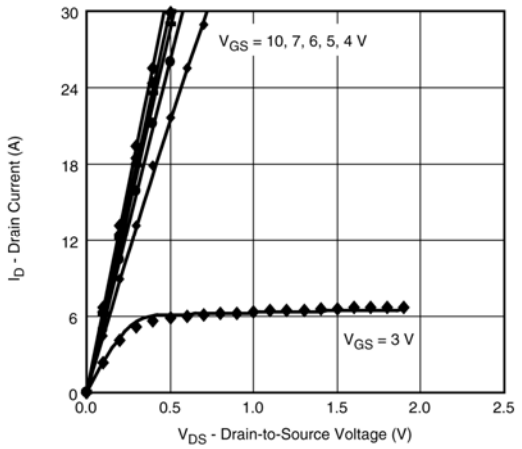
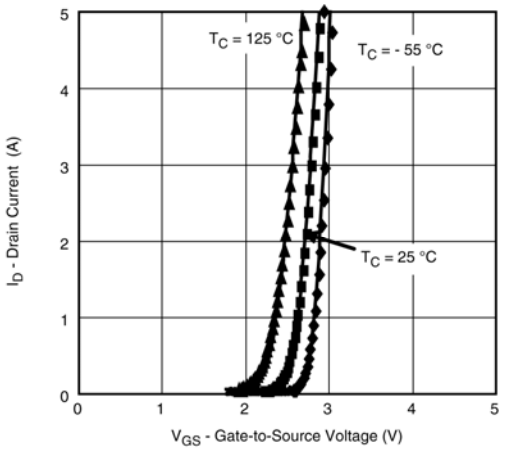


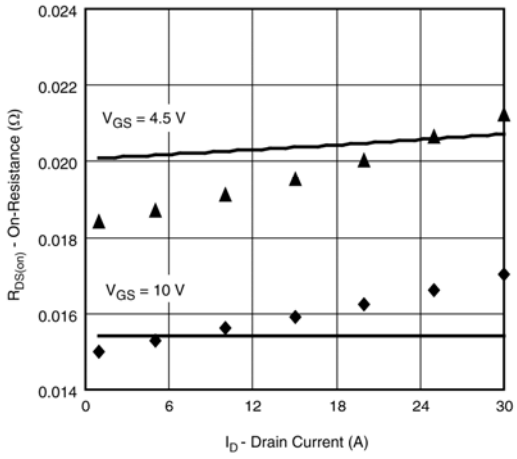


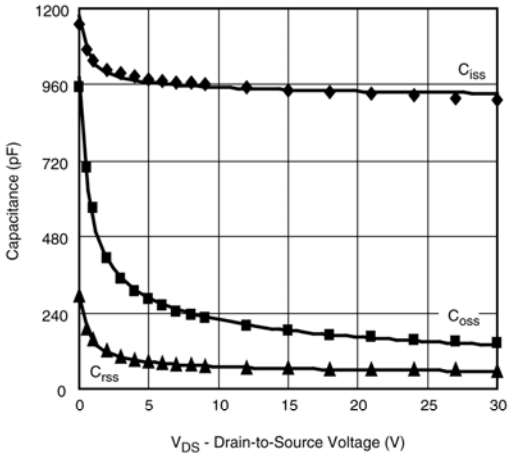
Note: Dots and squares represent measured data.

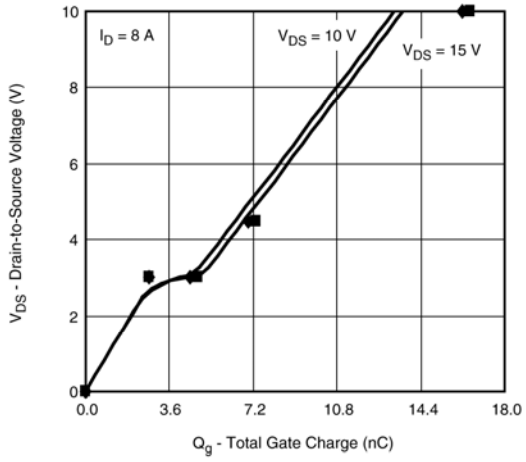
CHANNEL 2 - COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

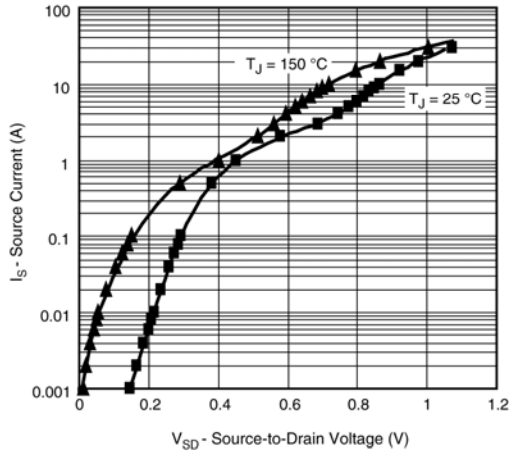












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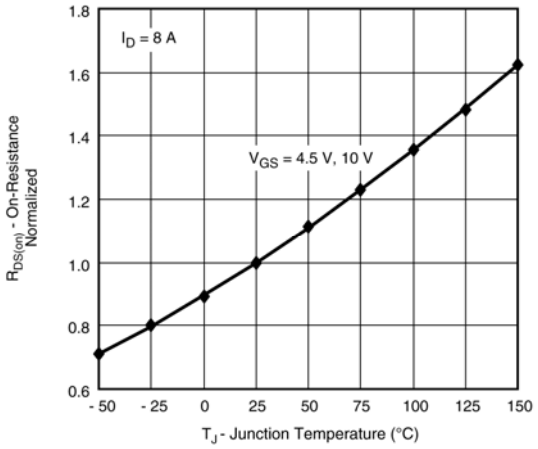
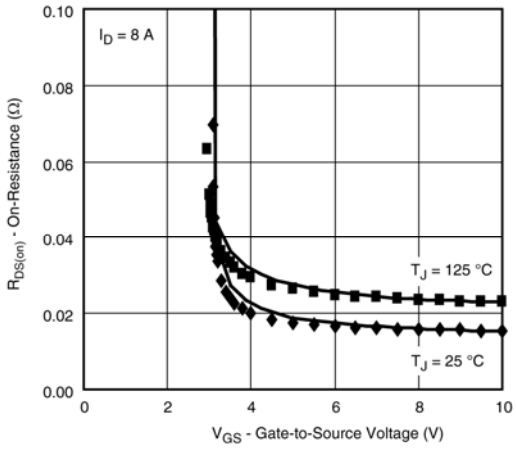
CHANNEL 2 - COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)





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